

isc Silicon NPN Power Transistor

BDY78

DESCRIPTION

- Continuous Collector Current- $I_C = 4A$
- Collector Power Dissipation-
: $P_C = 25W @ T_C = 25^\circ C$

APPLICATIONS

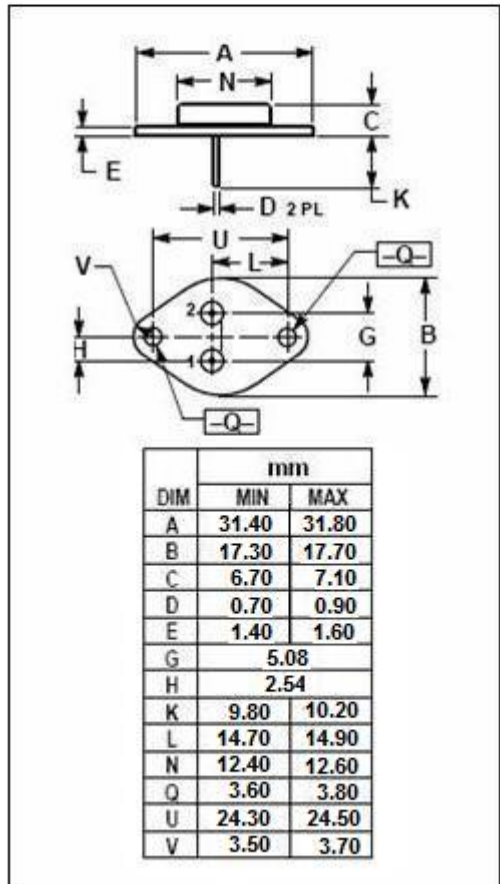
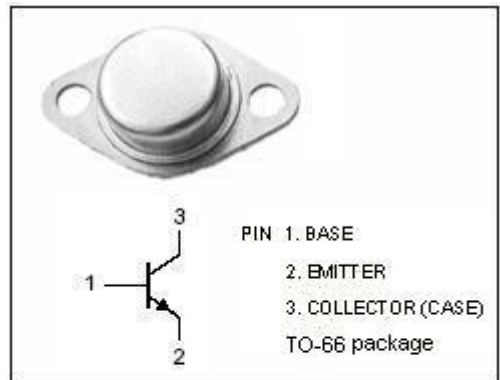
- Designed for general purpose switching and amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	90	V
V_{CEX}	Collector-Emitter Voltage $V_{BE} = -1.5V$	90	V
V_{CEO}	Collector-Emitter Voltage	55	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	25	W
T_J	Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature	-65~200	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	7.0	$^\circ C/W$



isc Silicon NPN Power Transistor**BDY78****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=100\text{mA}; I_B=0$	55		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	90		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=0.5\text{A}; I_B=50\text{mA}$		1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=1\text{A}$		3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=0.5\text{A}; V_{CE}=4\text{V}$		2.0	V
I_{CEX}	Collector Cutoff Current	$V_{CE}=90\text{V}; V_{BE}=-1.5\text{V}$ $V_{CE}=90\text{V}; V_{BE}=-1.5\text{V}; T_C=150^\circ\text{C}$		1.0 5.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$		1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=4\text{V}$	25	100	
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=4\text{V}$	5		
f_T	Current Gain-Bandwidth Product	$I_C=0.2\text{A}; V_{CE}=10\text{V}$	8		MHz